Contributions to DRD3/WP2-WP4

LGAD Sensor development Novel interconnection technologies for pixel detectors

G. Calderini, DI2I, Presentations des projets IN2P3 pour les DRDs, 4/03/2025

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Development of TI-LGAD for 4D tracking Project in DRD3/WP2

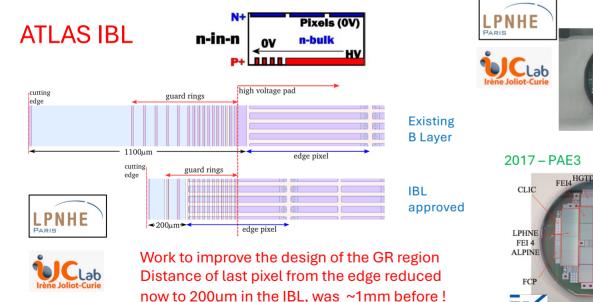
LPNHE / IJCLab

DRD3 WP2: Context for high-resistivity

Expertise in high resistivity sensor design and development at IN2P3 In the last decade applications to High Energy Physics in particular for LHC experiments

- early upgrades (example: ATLAS IBL)
- **HL-LHC** upgrades

Examples of complete contributions, from the sensor conception and gds to the final modules



Developments to achieve ATLAS ITk final design (n-in-p proof!)



Willing to maintain the expertise for many future applications

Structures for hybridization QC LPNHE responsible for final design at FBK

Applications of high-resistivity for future devices

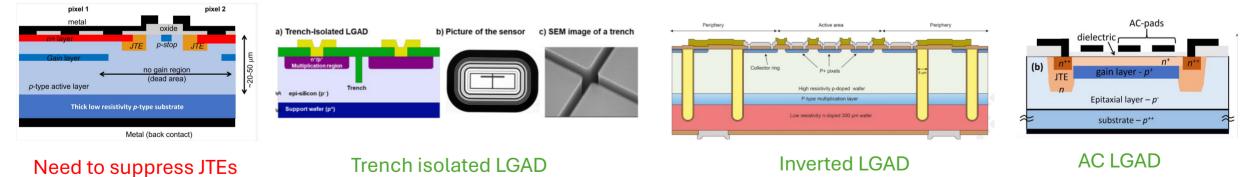
Most of the applications are based on time resolution

- replacement of HL-LHC (Phase-II) components
- timing layers at 30-50 ps for LHC experiments
- TOF large area layers (example EIC)
- 4D tracking

An excellent solution to match these requirements is given by LGAD

Very intense activity on LGAD in the sensor community in the last 5 years

Improve layout by suppressing Junction Terminations



Improve radiation hardness with carbon or compensating implantations

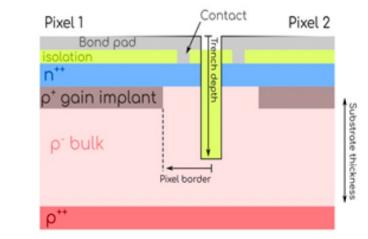
Our project in DRD3/WP2

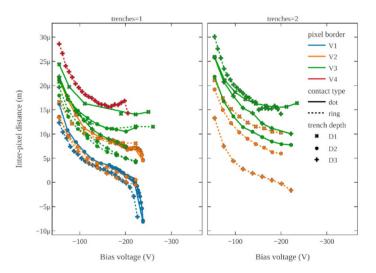
Work on improvement of present TI LGAD designs

Start from two existing TI-LGAD production (RD50 and AIDAInnova) and complete the characterization Proceed at one or two new submissions based on results, with optimized pixel layout, trench depth and carbon implantation

Main axes:

- Study the possible parameter of carbon implantation and optimize the radiation hardness to 5x10¹⁵ n_{eq}/cm2
- Achieve an Inter-Pixel distance of a few microns (<5 µm) before and after irradiation, through an optimization of the design and of the process
- Ensure a good yield for sensor structures compatible with read-out chips of a few cm^2 and pitches of the order of 50×50 μm^2
- Achieve a time resolution per hit around 30-40 ps





- Prototype sensors for upgrades of the ATLAS HGTD and possible upgrade of the CMS TEPX with 4D pixels, interest for very forward proton detectors close to ATLAS and CMS
- Explore the feasibility of implementing TI-LGAD sensors for TOF and particle identification in the outer layers of trackers for experiments at FCC-ee.

Participants in the project

Institute	Contact	Main areas of contribution
National Technical University of Athens (NTUA)	I. Kopsalis	Testing M1, M4, M6
University of California (UCSC)	S. Mazza	Testing M1, M5, M7
CERN	D. Dannheim	Hybridization M5, M7
CSIC	I. Vila	Testing M1, M5, M7
FBK	M. Boscardin	Production, simulations D1, D2
GSI Darmstadt	J. Pietraszko	Characterization, exchange of samples from a dedicated strip TI-LGAD production M5, M7
Hamburg University	J. Schwandt	Testing, simulations M1, M2, M5, M7
IJCLAB	A.Torrento	Testing M5, M7
IPE KIT	M. Caselle	Testing, Hybridization, Photonics applications M5, M7
JSI Ljubljana	G. Kramberger	Testing, irradiations, M5, M7
LIP Lisbon	J. J. Hollar	Testing, irradiations, simulations M1, M5, M7
LPNHE Paris	G. Calderini	Testing, Hybridization with ACF/ACP M5, M7
University of Montenegro	G. Medin	Testing M1, M5, M7
ORNL	M. Benoit	Testing, Hybridization, Irradiation M5, M7, D1
National Accelerator Center, Seville	Mª Carmen Jiménez Ramos	Ion Beam characterization M5, M7
Torino University	V. Sola	Simulations, Testing M1, M5, M7
Zurich University	A. Macchiolo	Testing, DAQ M1, M5, M7

Project structure

Project Work Package 1: Simulations and processing

Task 1: Sensor Optimization / TCAD simulations (collaboration with WG4)

Task 2: Processing at FBK of consecutive productions

Task 3: Physics Performance / Geometry Optimization

Project Work Package 2: Data acquisition and feedback to ASIC designer (collaboration with DRD7)

Task 1: Development of PCB boards to read-out test-structures / Read-out systems for timing chips

Task 2: Collection of requirements from the sensor side for the design of ASIC in 28 nm; link with DRD7 activities

Project Work Package 3: Testing & Characterization

Task 1: Characterization of the sensors in the lab with TCT and radioactive sources Task 2:Testing of the sensors with beam tests, to derive spatial and timing resolution before and after irradiation

Project Work Package 4: Irradiations

Task 1: Organization of irradiations (protons and neutrons) of the two TI-LGAD productions

Project Work Package 5: Hybridization

Task 1: Organization of hybridization for the two TI-LGADs production

Milestones / Deliverables

Number	Deliverable/Milestone Title	WP project #	Lead	Туре	Dissemination Level	Due Date
M1	Report on radiation hardness studies of TI-LGAD structures from RD50 (no-carbon) and AIDAinnova runs (w/ carbon)	3	Santander, Ljubljana?	Report	DRD3 report	Month 12 (Q4 2025)
M2	Comparison of observed performance with TCAD simulations	1, 3	UHH, Torino	Report	DRD3 report	Month 18 (Q2 2026)
М3	Design of the first TI-LGAD production within DRD3	1	FBK	Layout	DRD3 report	Month 12 (Q4 2025)
D1	First production of small area TI-LGAD structures, to optimize radiation hardness, timing and yield	1	FBK	Prototype	Publication	Month 18 (Q2 2026)
M4	Design and production of a multi-pad PCB board for the read-out of LGAD test- structures	2,3	КІТ	Board	DRD3 report	Month 18 (Q2 2026)
M5	Characterization of the devices of first production before and after irradiation	3,4,5	UZH, Torino	Report	Publications/ DRD3 report	Month 30 (Q2 2027)
M6	Design of second production of TI-LGAD structures compatible with full scale timing ASICS.	1	FBK	Layout	DRD3 report	Month 36 (Q4 2027)
D2	Second production of larger area TI-LGAD structures, compatible with full scale ASICs	1	FBK	Prototype	Publication	Month 42 (Q2 2028)
Μ7	Characterization of the devices of first production before and after irradiation	3,4,5	LPNHE / IJCLab (proposed; subject to Review)	Report	Publications/ DRD3 report	Month 48 (Q4 2028)

Personnel in France

Person		FTEs (total months)
LPNHE		
G. Calderini	DR	4
R. Camacho	CR	4
Non-permanent (AIDA)	Post-doc	6
F. Crescioli	IR	4
IJCLab		
A. Torrento	IR	6

Premiere estimation des demandes budgetaires (à definer mieux dans la suite)

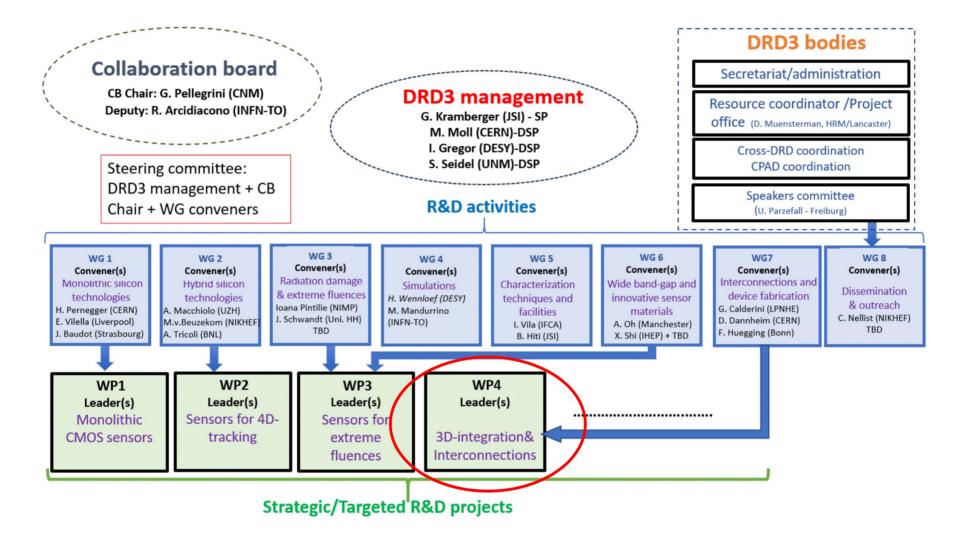
In total, over the experiment (2025-2027)

- ~ 20K contribution to productions + 10K hybridization
- ~ 5K small equipment
- ~5K consommables
- ~ 6K missions (2025-27)

In-house plating, hybridization and module integration technologies for pixel detectors

Project in DRD3/WP4

DRD3 WP4: Interconnections technologies



One of the four ECFA strategic axes for solid state detectors, translated in the 4 WP of DRD3

DRD3 WP4: Context for interconnections

Need to provide fast, cheap and reliable interconnection technology (pixel die-todie but also die-to-flex)

This will boost the R&D in laboratories

Advantages:

- Single die processing
- Adaptable to the application
- Low temperature process
- Maskless
- In-house (short turnaround time, quick adjustments)
- Cheap

Some possible solutions

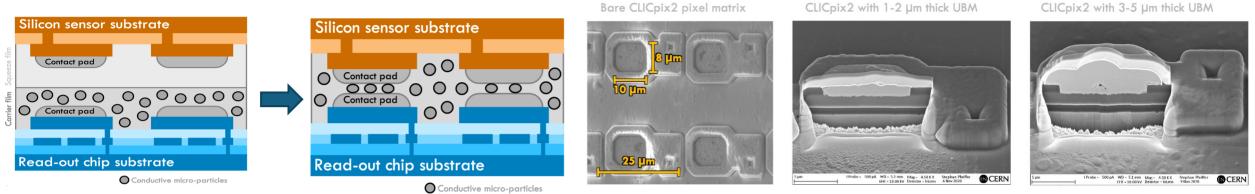
- Use of Anisotropic Conductive Films (ACF) or Pastes (ACP)

UBM is still required to obtain the particle adhesion, but it is a wet chemical deposition of Ni and Au (maskless process, low cost)

- Interconnection via gold stud deposition

ACF/ACP

Existing activity to use ACF/ACP in the framework of AIDAInnova (and now DRD3 project)



See: P. Svihra,

https://indico.cern.ch/event/1104064/contributions/4789884/attachments/2416826/4135907/svihra AIDA2022 ACF update.pdf or A. Lale et al. "Pixel detector hybridization with anisotropic conductive adhesives" PIXEL 2024, Strasbourg, 18-22/11/2024 https://indico.in2p3.fr/event/32425/contributions/142775/

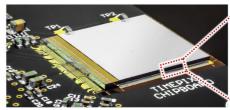
In-house post-processing of devices: Nickel-Gold (ENIG), mask-less

- Deposition of epoxy film or compound with small (3-5µm) conductive particles
- Film or paste produced by company; can be optimized depending on the device
- Thermo-compression: 150C, 500N/cm2
- Being demonstrated in AIDAInnova but only preliminary results

Need full process optimization and validation in real conditions

(mechanical and thermal stress, radiation hardness)

G. Calderini, DI2I, Presentations des pro







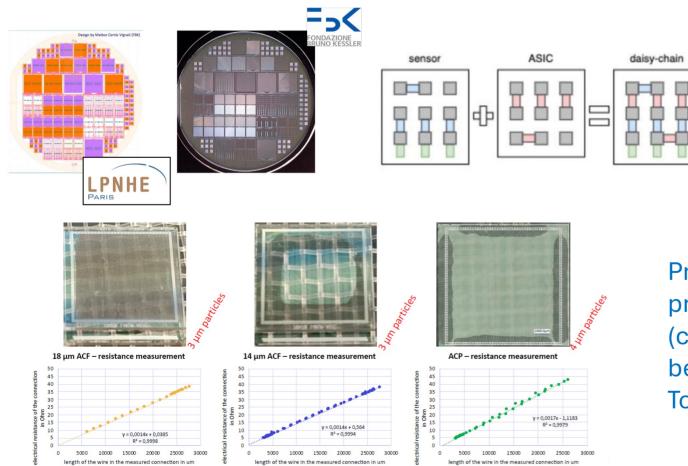
CLICpix2 with 3-5 µm thick UBM

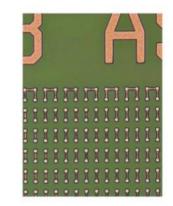


Characterisation tools

Yield optimization depending on device characteristics (pixel pitch, device size etc)

Wafer layout with different sensor types has been designed at LPNHE in collaboration with FBK which then produced it; system of conductive chains to measure the interconnection reliability and yield





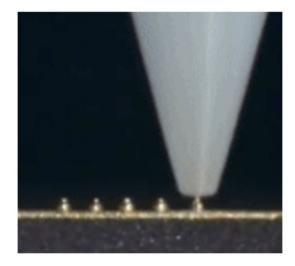
	pitch	size in mm	connections	per wafer	type
160x160 20um	20 um	3.2 x 3.2	25600	36	grid
CLICpix2	25 um	3.2 x 3.2	16384	34	grid
400x400 25um	25 um	20 x 20	640000	5	grid
Timepix3	55 um	14 x 14	65536	4	grid
Timepix3 islands	55 um	14 x 14	65536	4	grid
RD53	50 um	20 x 20	160000	4	grid
RD53 islands	50 um	20 x 20	160000	2	grid
70x70 140um	140 um	20 x 20	2112	3	periphera
10x10 1000um	1000 um	20 x 20	400	3	grid
3x3 4500um	4500 um	20 x 20	36	1	grid

Preliminary measurements on the very first prototypes indicate very good conductivity (connection resistance <1 Ohm) and yield between 98 and 99% To be studied more systematically

Gold stud hybridization test

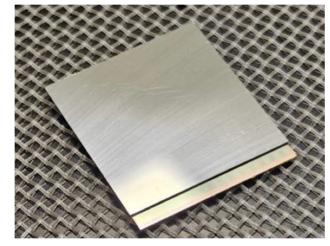
ALTIROC3/A and LGAD sensors from ATLAS High Granularity Timing Detector (HGTD)

• Single and stacked double gold studs used for the connections between the chips, epoxy underfill for bonding



Gold studs are deposited one by one

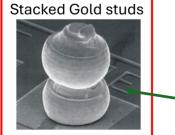
ALTIROC/LGAD Hybrid Flip-chip done with NCP (Araldite 2011)



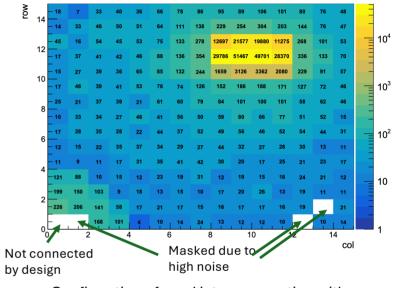
Gold stud



Pictures from Hybrid SA



Preferred this solution to increase the gap between ASIC and sensor from 20 µm to 35 µm and thereby decrease coupling between them Test-beam occupancy map of ALTIROC with double gold studs + irradiated LGAD sensor



Confirmation of good inter-connection with occupancy map (\approx 100%)

- High connection yield, reproducibility, low temperature process
- Only for large pitch (>100µm), large pads (>80µm) chips

Our project in DRD3/WP4

This project targets the development of scalable and cost-effective in-house plating, hybridisation and module-integration technologies. The main development objectives in the different technology areas are:

- Development of an in-house Ni/Au plating process suitable for single dies and a wide range of interconnect pitches (25 microns to several mm) and interface topologies
- Development of very thin hybrid pixel modules using alternative in-house interconnection technologies such as Anisotropic Conductive Films (ACF) or Pastes (ACP), nanowires, solder-jet printing, gold-stud bonding;
- Study of die-to-die 3D interconnection techniques to achieve highly integrated modules, using RDLs (Redistribution Layers) and other enabling interconnection techniques such as mentioned above; validation in a first phase for general R&D and demonstrator-module building using monolithic chips or hybrid assemblies from the participating sensor and ASIC R&D projects;
- Integration of modules for hybrid and CMOS pixel detectors for low mass large-area detectors; studies to combine electrical and mechanical connections to achieve a compact module layout; studies to integrate optical data transmission using existing developments from collaborating projects;
- Characterization of produced test devices in terms of interconnect yield and quality: mechanical (cross sections) and functional (radioactive sources, particle beams) tests.
- Reliability testing of produced test devices: accelerated ageing / thermal cycling, radiation hardness; mechanical (delamination) and functional tests.

Participants

Institute	Contact	Main areas of contribution
LPNHE Paris	G. Calderini	Testing, development of test devices
FBK Trento	M. Boscardin	Development of test devices, hybridisation, flex developments
CERN	D. Dannheim	Plating, hybridisation, module integration, flex developments, testing
University of Geneva	M. Vicente	Hybridisation, module integration

(CONPART, Norway, partner commercial)

(everybody interested is welcome to join!)

Project structure

Project Work Package 1: Plating

- Task 1: ENIG plating for different test chain devices and process optimisation for different pitches, pad sizes and matrix areas
- Task 2: ENIG plating for functional sensor, ASIC and PCB samples from the collaborating projects

Project Work Package 2: Hybridisation

- Task 1: Evaluation of different hybridisation processes using chain devices
- Task 2: Hybridisation of functional samples from different projects
- Task 3: Design and production of dedicated chain devices for plating and interconnect tests

Project Work Package 3: Module integration

- Task 1: Demonstration of flip-chip module integration with suitable ASICs and test boards
- Task 2: Development of flex-PCB for multi-chip module integration demonstrator
- Task 3: Integration of silicon photonics integrated circuits from collaborating projects to build demonstrator modules and study their integration

Project Work Package 4: Testing

- Task 1: Electrical and functional testing of produced chain devices, functional hybrids and module demonstrators
- Task 2: Thermal-cycling and mechanical robustness studies with chain devices, functional hybrids and module demonstrators
- Task 3: Radiation-hardness testing of functional hybrids and module demonstrators

Milestones / Deliverables

Number	Deliverable/Milestone Title	Project WP #	Lead	Туре	Dissemination Level	Due Date
M1	Characterisation of existing interconnect-test devices	4	LPNHE, CERN	Report	DRD3 report or publication	Month (Q2 2025)
D1	New interconnect test devices produced	1, 2	FBK, LPNHE	Prototype	DRD3 report or publication	Month 30 (Q2 2026)
D2	Optimised plating process developed	1	CERN	Report	DRD3 report or publication	Month 48 (Q4 2026)
M2	Characterisation of assemblies with new interconnect-test devices	2, 4	LPNHE, CERN	Report	DRD3 report or publication	Month 42 (Q3 2027)
D3	Single-die hybridisation process developed	2	UNIGE, CERN	Report	DRD3 report or publication	Month 48 (Q4 2027)
D4	Module flex developed	3	CERN, FBK	Prototype	DRD3 report or publication	Month 48 (Q4 2027)
D5	Reliability testing	4	LPNHE, CERN	Report	DRD3 report or publication	Month 48 (Q4 2027)

Personnel

Person		FTEs (total months)
LPNHE		
G. Calderini	DR	4
B. Laforge	PR	4
Non-permanent (AIDA)	Post-doc	6
F. Crescioli	IR	4
N. Garroum	IR	4
Y. Orain	AI	4

Premiere estimation des demandes budgetaires (à definer mieux dans la suite)

In total, over the full experiment (2025-2027, and considering some tens of KE from AIDAInnova in 2025)

- ~ 12K contribution ACF/ACP
- ~ 5K small equipment
- ~6K consummables
- ~9K testbeams/irradiations
- ~ 6K missions (2025-27)

Next steps for the two projects

- Finalization of participants' names and contributions
- Update of Fiches Projet with the common template (almost finished)
- Consolidation of synergies with other DRD projects